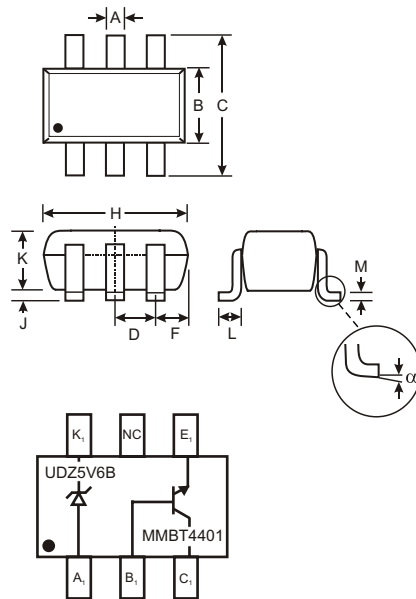


Features

- Epitaxial Planar Die Construction
- Ideally Suited for Automated Assembly Processes
- Available in Lead Free/RoHS Compliant Version (Note 2)

Mechanical Data

- Case: SOT-26
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Solderable per MIL-STD-202, Method 208
- Also Available in Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe). Please see Ordering Information, Note 5, on Page 5
- Marking: AH1
- Marking & Type Code Information: See Last Page
- Ordering Information: See Last Page
- Weight: 0.008 grams (approx.)



SOT-26			
Dim	Min	Max	Typ
A	0.35	0.50	0.38
B	1.50	1.70	1.60
C	2.70	3.00	2.80
D	—	—	0.95
F	—	—	0.55
H	2.90	3.10	3.00
J	0.013	0.10	0.05
K	1.00	1.30	1.10
L	0.35	0.55	0.40
M	0.10	0.20	0.15
α	0°	8°	—
All Dimensions in mm			

Maximum Ratings, NPN Transistor Element @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CB0}	60	V
Collector-Emitter Voltage	V_{CE0}	40	V
Emitter-Base Voltage	V_{EB0}	6.0	V
Collector Current - Continuous (Note 1)	I_C	600	mA

Maximum Ratings, Zener Element @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Forward Voltage @ $I_F = 10\text{mA}$	V_F	0.9	V

Thermal Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 1)	P_d	300	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Operating and Storage and Temperature Range	T_j, T_{STG}	-55 to +150	$^\circ\text{C}$

- Notes:
1. Part mounted on FR-4 board with recommended pad layout, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
 2. No purposefully added lead.

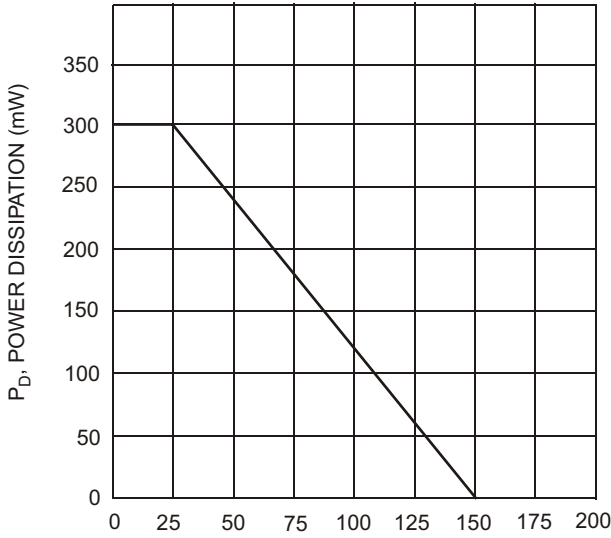
Electrical Characteristics, NPN Transistor Element @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 3)					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	60	—	V	$I_C = 100\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	40	—	V	$I_C = 1.0\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6.0	—	V	$I_E = 100\mu\text{A}, I_C = 0$
Collector Cutoff Current	I_{CEX}	—	100	nA	$V_{CE} = 35\text{V}, V_{EB(OFF)} = 0.4\text{V}$
Base Cutoff Current	I_{BL}	—	100	nA	$V_{CE} = 35\text{V}, V_{EB(OFF)} = 0.4\text{V}$
ON CHARACTERISTICS (Note 3)					
DC Current Gain	h_{FE}	20 40 80 100 40	— — — 300 —	—	$I_C = 100\mu\text{A}, V_{CE} = 1.0\text{V}$ $I_C = 1.0\text{mA}, V_{CE} = 1.0\text{V}$ $I_C = 10\text{mA}, V_{CE} = 1.0\text{V}$ $I_C = 150\text{mA}, V_{CE} = 1.0\text{V}$ $I_C = 500\text{mA}, V_{CE} = 2.0\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	0.40 0.75	V	$I_C = 150\text{mA}, I_B = 15\text{mA}$ $I_C = 500\text{mA}, I_B = 50\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	0.75 —	0.95 1.2	V	$I_C = 150\text{mA}, I_B = 15\text{mA}$ $I_C = 500\text{mA}, I_B = 50\text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{cb}	—	6.5	pF	$V_{CB} = 5.0\text{V}, f = 1.0\text{MHz}, I_E = 0$
Input Capacitance	C_{eb}	—	30	pF	$V_{EB} = 0.5\text{V}, f = 1.0\text{MHz}, I_C = 0$
Input Impedance	h_{ie}	1.0	15	k Ω	$V_{CE} = 10\text{V}, I_C = 1.0\text{mA}, f = 1.0\text{kHz}$
Voltage Feedback Ratio	h_{re}	0.1	8.0	$\times 10^{-4}$	
Small Signal Current Gain	h_{fe}	40	500	—	
Output Admittance	h_{oe}	1.0	30	μS	
Current Gain-Bandwidth Product	f_T	250	—	MHz	$V_{CE} = 10\text{V}, I_C = 20\text{mA}, f = 100\text{MHz}$
SWITCHING CHARACTERISTICS					
Delay Time	t_d	—	15	ns	$V_{CC} = 30\text{V}, I_C = 150\text{mA}, V_{BE(off)} = 2.0\text{V}, I_{B1} = 15\text{mA}$
Rise Time	t_r	—	20	ns	
Storage Time	t_s	—	225	ns	$V_{CC} = 30\text{V}, I_C = 150\text{mA}, I_{B1} = I_{B2} = 15\text{mA}$
Fall Time	t_f	—	30	ns	

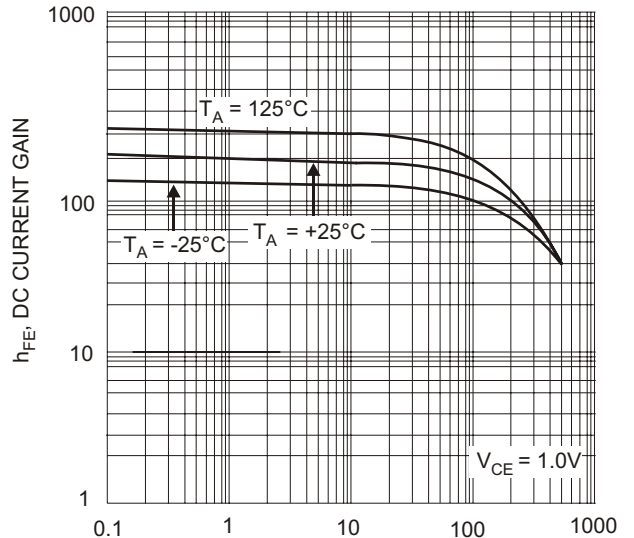
Electrical Characteristics, Zener Element @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Type Number	Zener Voltage Range (Note 3)				Maximum Zener Impedance		Maximum Reverse Leakage Current	
	$V_Z @ I_{ZT}$			I_{ZT}	$Z_{ZT} @ I_{ZT}$	$Z_{ZK} @ I_{ZK} = 0.5\text{mA}$	I_R	@ V_R
	Nom (V)	Min (V)	Max (V)	mA	Ω		μA	V
UDZ5V6B	5.6	5.49	5.73	5	60	200	1.0	2.5

Notes: 3. Short duration test pulse used to minimize self-heating effect.



T_A , AMBIENT TEMPERATURE (°C)
Fig. 1 Max Power Dissipation vs Ambient Temperature (Total Device)



I_C , COLLECTOR CURRENT (mA)
Fig. 2 Typical DC Current Gain vs Collector Current

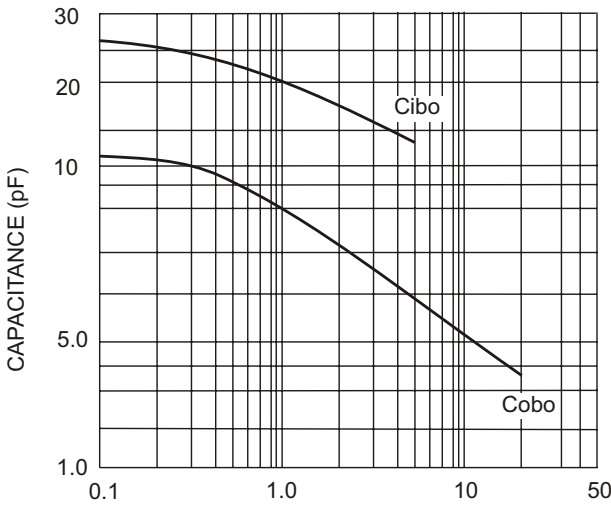
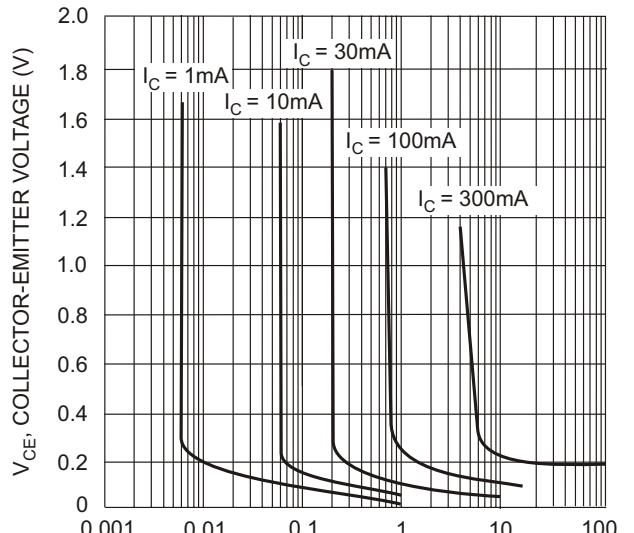


Fig. 3 Typical Capacitance



I_B , BASE CURRENT (mA)
Fig. 4 Typical Collector Saturation Region

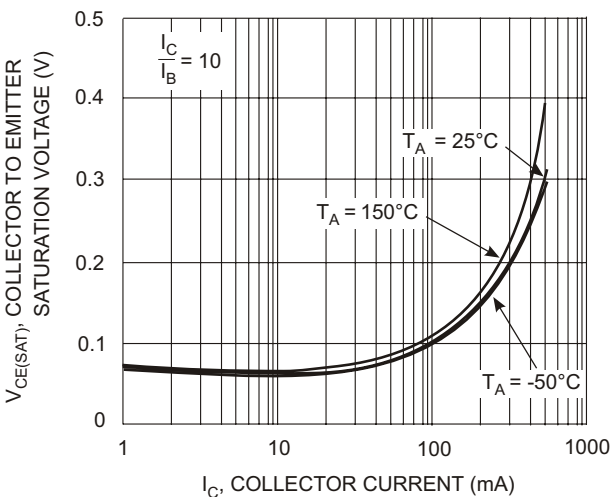


Fig. 5 Collector Emitter Saturation Voltage vs. Collector Current

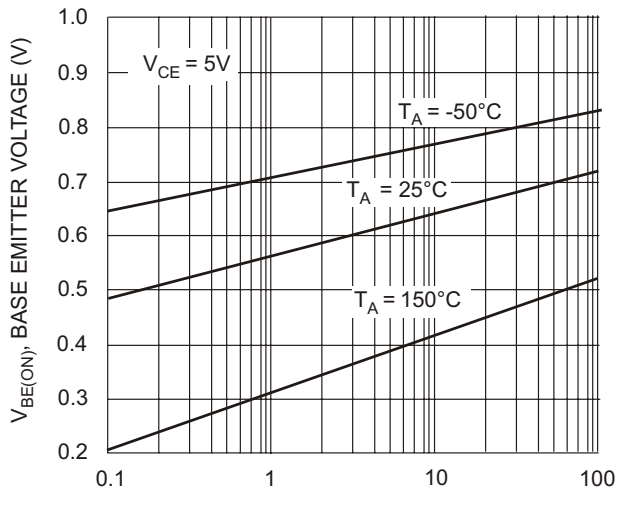


Fig. 6 Base Emitter Voltage vs. Collector Current

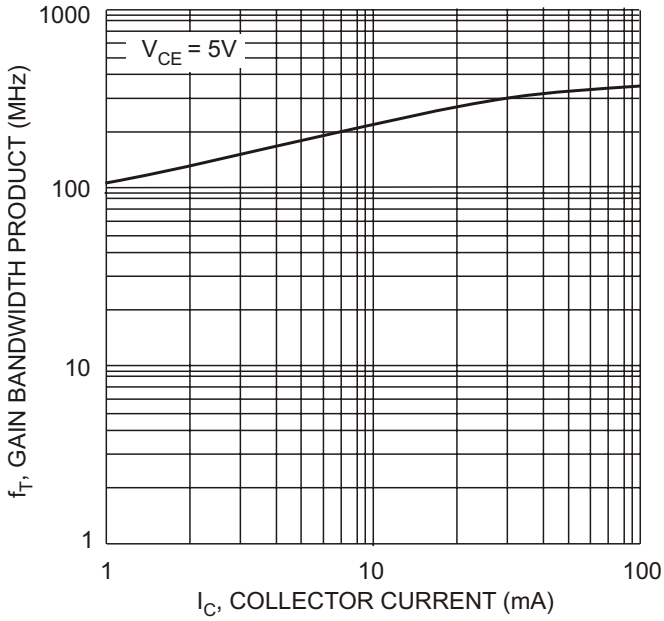


Fig. 7 Gain Bandwidth Product vs. Collector Current

Zener Section

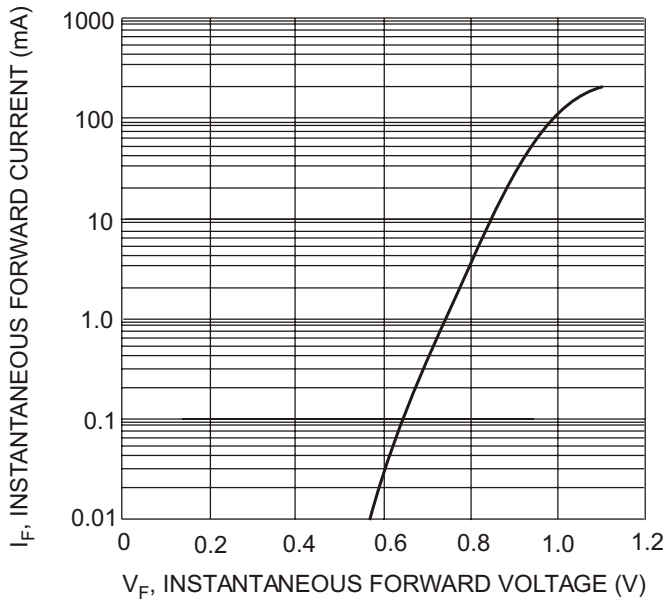


Fig. 8 Typical Forward Characteristics

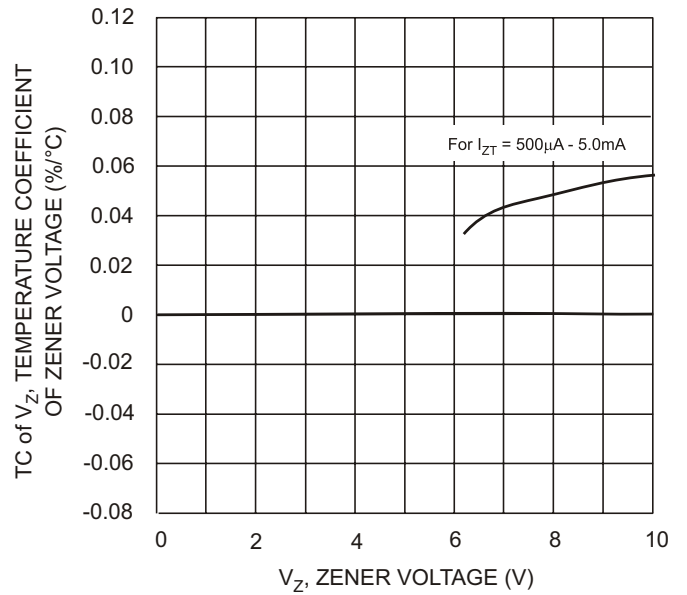


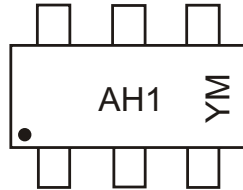
Fig. 9 Typical Temperature Coefficient of Zener Voltage vs. Zener Voltage, UDZ5V6B

Ordering Information (Note 4)

Device	Packaging	Shipping
DVRN6056-7	SOT-26	3000/Tape & Reel

- Notes:
- For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.
 - For Lead Free/RoHS Compliant version part number, please add "-F" suffix to the part number above. Example: DVRN6056-7-F.

Marking Information



AH1 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year ex: P = 2003
 M = Month ex: 9 = September

Date Code Key

Year	2003	2004	2005	2006	2007	2008	2009
Code	P	R	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D